

Claim Amendment

1-4. (canceled)

sub C1
5. (previously amended) A structure of claim 17, wherein the drain contact region is split into at least one first drain contact portion located near the gate, and at least one second drain contact portion.

6. (canceled)

C2 sub
7. (previously amended) A structure of claim 17, wherein the structure includes multiple emitters outside at least part of the drain contact region.

8-10. (withdrawn)

sub C3
11. (currently amended) A high holding voltage LVTSCR-like structure, comprising an emitter, a drain contact region, and a floating drain, wherein the emitter is located so that at least part of the drain contact region is located between ~~the~~ a gate and the emitter.

12. (currently amended) A structure of claim 11, wherein the drain contact region is split into at least one first drain portion located near the gate, and at least one second drain portion.

13. (canceled)

C4 sub
14. (original) A structure of claim 11, wherein the emitter comprises a plurality of emitter regions.

15. (original) A structure of claim 12, wherein the emitter comprises a plurality of emitter regions.

C5 sub
16. (currently amended) A structure of claim 12, wherein the floating drain and drain contact region are separated by a shallow trench isolation region.

C6 sub
17. (previously added) A LVTSCR-like ESD protection structure, comprising a drain contact region, a p+ emitter, and a gate, wherein at least part of the drain contact region is located between the p+ emitter and the gate.

18.

(previously added) A structure of claim 17, further comprising a floating drain located between the gate and the p+ emitter.
